



1 Overview

Features

- Current controlled input
- Capable of driving all kind of loads (inductive, capacitive and resistive)
- Negative voltage clamped at output with inductive loads
- Current limitation
- Very low standby current
- Thermal shutdown with restart
- Overload protection
- Short circuit protection
- Overvoltage protection (including load dump)
- Reverse battery protection
- Loss of GND and loss of V_{bb} protection
- ESD-Protection
- Improved electromagnetic compatibility (EMC)
- Green Product (RoHS compliant)

ITS41k0S-ME-N is not qualified and manufactured according to the requirements of Infineon Technologies with regards to automotive and/or transportation applications.

Description

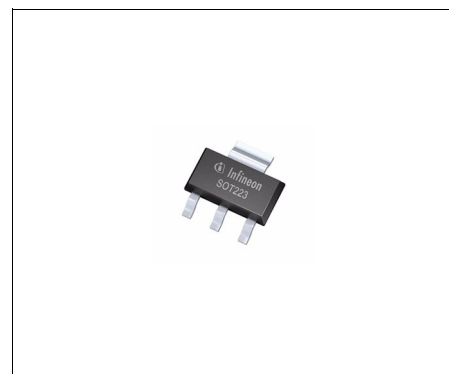
The ITS41k0S-ME-N is a protected 1 Ω single channel Smart High-Side NMOS-Power Switch in a PG-SOT223-4 package with charge pump and current controlled input, monolithically integrated in a smart power technology.

Product Summary

Overvoltage protection $V_{SAZ\ min} = 62V$
 Operating voltage range $4,9V < V_S < 60V$
 On-state resistance $R_{DS\ ON}$ typ 800 m Ω
 Operating Temperature range $T_j = -40^{\circ}C$ to $125^{\circ}C$

Application

- All types of resistive, inductive and capacitive loads
- Current controlled power switch for 12V, 24V and 45V DC in industrial applications
- Driver for electromagnetic relays
- Signal amplifier



PG-SOT223-4

Type	Package	Marking
ITS41k0S-ME-N	PG-SOT223-4	I1k0SN

2 Block Diagram and Terms

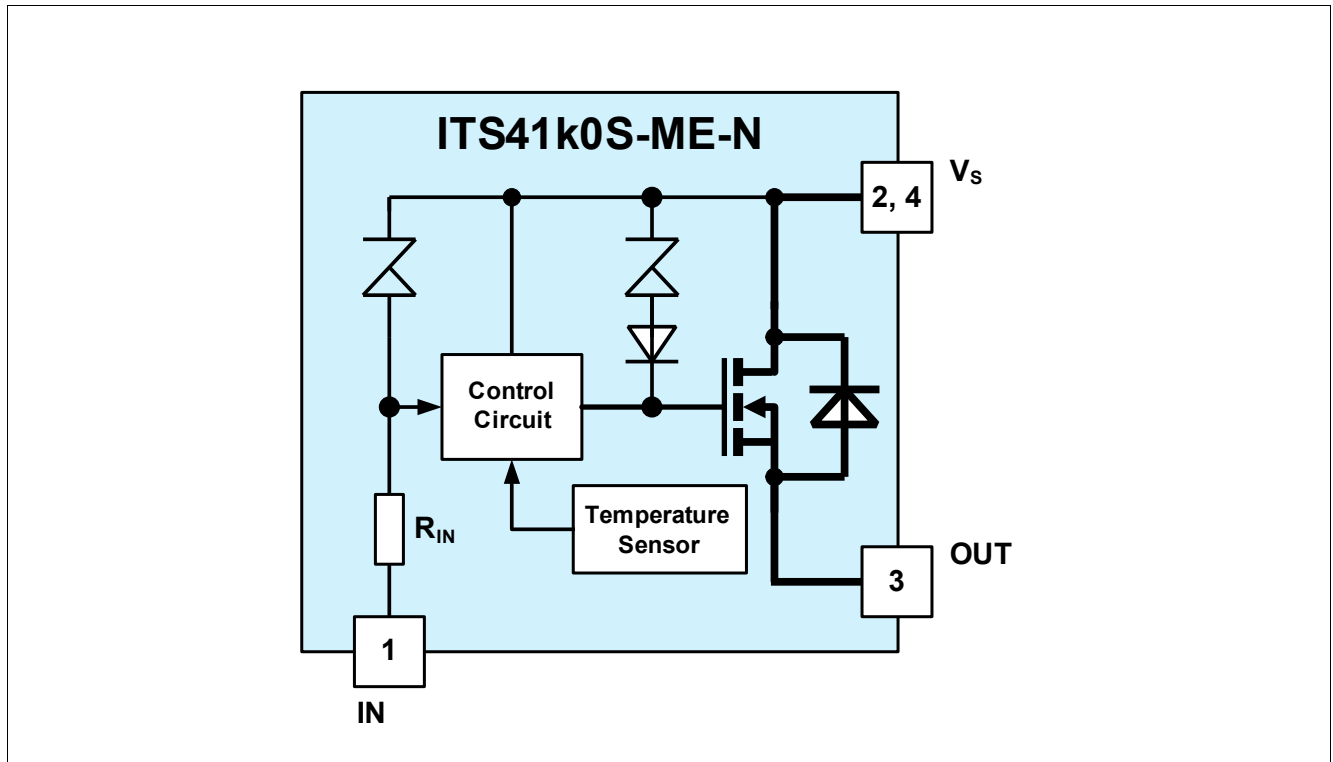


Figure 1 Block diagram

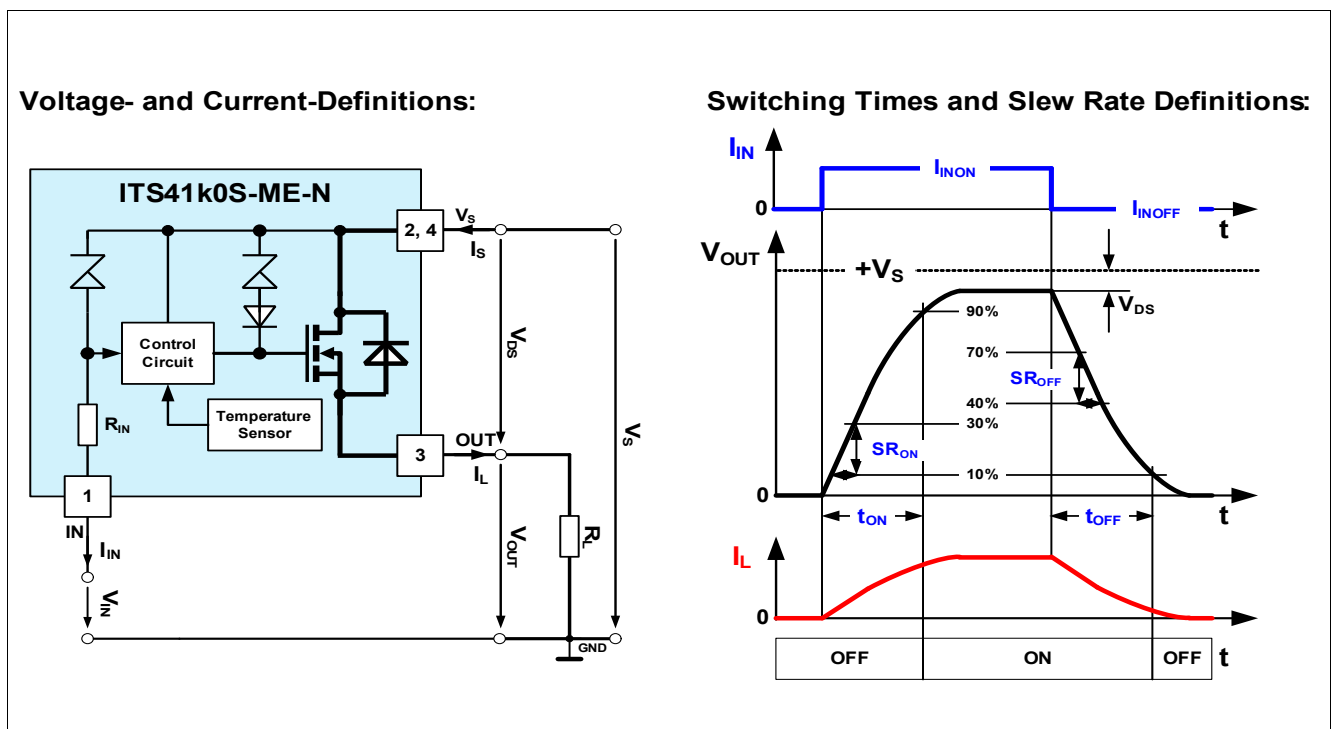


Figure 2 Terms - parameter definition

3 Pin Configuration

3.1 Pin Assignment

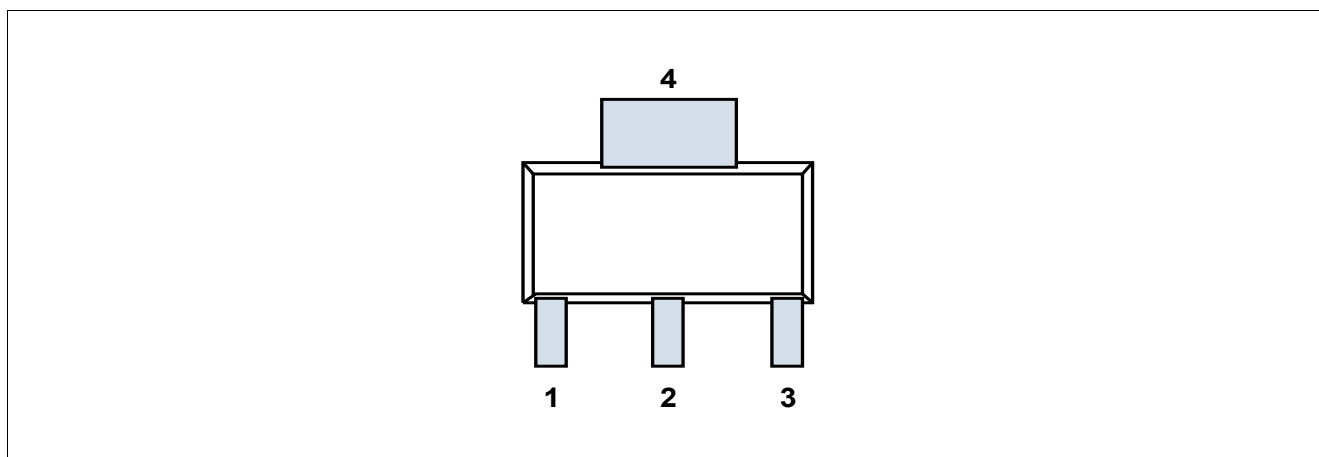


Figure 3 Pin configuration top view, PG-SOT223-4

3.2 Pin Definitions and Functions

Pin	Symbol	Function
1	IN	Input, activates the power switch in case of connection to GND
2	VS	Supply voltage
3	OUT	Output to the load
4	VS	Supply voltage

4 General Product Characteristics

4.1 Absolute Maximum Ratings

Table 1 Absolute maximum ratings ¹⁾T_j = 25°C all voltages with respect to ground.
Currents flowing into the device unless otherwise specified in chapter "Block Diagram and Terms"

Parameter	Symbol	Values			Unit	Note / Test Co ndition
		Min.	Typ.	Max.		
Supply voltage VS						
Voltage	V _S		60	V		4.1.1
Output stage OUT						
Output Current; (Short circuit current see electrical characteristics)	I _{OUT}	self limited			A	4.1.2
Input IN						
Input Current	I _{IN}	-15	15	mA		4.1.3
Temperatures						
Junction Temperature	T _j	-40	125	°C		4.1.4
Storage Temperature	T _{stg}	-55	125	°C		4.1.5
Power dissipation						
Ta = 25 °C ²⁾	P _{tot}		1.7	W		4.1.6
Inductive load switch-off energy dissipation						
Tj = 150 °C; IL=0.15A; single pulse ¹⁾	E _{AS}		1000	mJ		4.1.7
ESD Susceptibility						
ESD susceptibility (input pin)	V _{ESD}	-1	1	kV	HBM ³⁾	4.1.8
ESD susceptibility (all other pins)	V _{ESD}	-5	5	kV	HBM ³⁾	4.1.9

1) Not subject to production test, specified by design

2) Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6 cm² (one layer, 70mm thick) copper area for V_{bb} connection. PCB is vertical without blown air

3) ESD susceptibility HBM according to EIA/JESD 22-A 114.

Note: Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" the normal operating range. Protection functions are not designed for continuous or repetitive operation.

4.2 Functional Range

Table 2 Functional Range

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
Nominal Operating Voltage	V_S	4.9	–	60	V	V_S increasing	4.2.1

Note: Within the functional range the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the related electrical characteristics table.

4.3 Thermal Resistance

This thermal data was generated in accordance with JEDEC JESD51 standards.

More information on www.jedec.org.

Table 3 Thermal Resistance¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
PG-SOT223-4							
Junction to Case, Exposed pad	R_{thjc}	—	40.5	—	K/W		4.3.1
Junction to ambient	R_{thJA_1s0p}	—	145.4	—	K/W	2)	4.3.2
Junction to ambient	$R_{thJA_1s0p_300mm}$	—	77.2	—	K/W	3)	4.3.3
Junction to ambient	$R_{thJA_1s0p_600mm}$	—	66.2	—	K/W	4)	4.3.4
Junction to ambient	R_{thJA_2s2p}	—	57.8	—	K/W	5)	4.3.5
Junction to ambient	$R_{thJA_2s2pvia}$	—	52.9	—	K/W	6)	4.3.6

1) Not subject to production test, specified by design

2) Specified R_{thJA} value is according to Jedec JESD51-3 at natural convection on FR4 1s0p board, footprint; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 1x 70μm Cu.

3) Specified R_{thJA} value is according to Jedec JESD51-3 at natural convection on FR4 1s0p board, Cu, 300mm²; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 1x 70μm Cu.

4) Specified R_{thJA} value is according to Jedec JESD51-3 at natural convection on FR4 1s0p board, 600mm²; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 1x 70μm Cu.

5) Specified R_{thJA} value is according to Jedec JESD51-2,-5,-7 at natural convection on FR4 2s2p board; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 2 inner copper layers (2 x 70μm Cu, 2 x 35μm Cu).

6) Specified R_{thJA} value is according to Jedec JESD51-2,-5,-7 at natural convection on FR4 2s2p board with two thermal vias; the Product (Chip+Package) was simulated on a 76.2 x 114.3 x 1.5 mm board with 2 inner copper layers (2 x 70μm Cu, 2 x 35μm Cu). The diameter of the two vias are equal 0.3mm and have a plating of 25μm with a copper heatsink area of 3mm x 2mm). JEDEC51-7: The two plated-through hole vias should have a solder land of no less than 1.25 mm diameter with a drill hole of no less than 0.85 mm diameter.

5 Electrical Characteristics

Table 4 $V_S = 9V$ to $60V$; $T_j = -40^\circ C$ to $125^\circ C$; all voltages with respect to ground. Currents flowing into the device unless otherwise specified in chapter "Block Diagram and Terms". Typical values at $V_S = 13.5V$, $T_j = 25^\circ C$

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
Powerstage							
NMOS ON Resistance	$R_{\text{DS(on)}}$	—	0.8	1.5	Ω	$I_{\text{OUT}} = 150\text{mA}$; $T_{\text{j}} = 25^{\circ}\text{C}$; IN conected to GND	5.0.1
NMOS ON Resistance	$R_{\text{DS(on)}}$	—	1.5	3.0	Ω	$I_{\text{OUT}} = 150\text{mA}$; $T_{\text{j}} = 125^{\circ}\text{C}$; IN conected to GND	5.0.2
NMOS ON Resistance	$R_{\text{DS(on)}}$	—	2	5	Ω	$I_{\text{OUT}} = 50\text{mA}$; $T_{\text{j}} = 25^{\circ}\text{C}$; $V_{\text{S}} = 6\text{V}$; IN conected to GND	5.0.3
Nominal Load Current ¹⁾ ; device on PCB ²⁾	I_{LNOM}	0.2	—	—	A	$T_{\text{a}} = 85^{\circ}\text{C}$; $T_{\text{j}} = 125^{\circ}\text{C}$;	5.0.4
Timings of Power Stages							
Turn ON Time ³⁾ (to 90% of V_{out}); V_{S} to GND transition of V_{IN}	t_{ON}	—	—	125 ⁴⁾	μs	$V_{\text{S}} = 13.5\text{V}$; $R_{\text{L}} = 270\Omega$	5.0.5
Turn ON Time ³⁾ (to 90% of V_{out}); V_{S} to GND transition of V_{IN}	t_{ON}	—	45	100	μs	$V_{\text{S}} = 13.5\text{V}$; $R_{\text{L}} = 270\Omega$; $T_{\text{j}} = 25^{\circ}\text{C}$	5.0.6
Turn OFF Time ³⁾ (to 10% of V_{out}); GND to V_{S} transition of V_{IN}	t_{OFF}	—	—	175 ⁴⁾	μs	$V_{\text{S}} = 13.5\text{V}$; $R_{\text{L}} = 270\Omega$	5.0.7
Turn OFF Time ³⁾ (to 10% of V_{out}); GND to V_{S} transition of V_{IN}	t_{OFF}	—	40	140	μs	$V_{\text{S}} = 13.5\text{V}$; $R_{\text{L}} = 270\Omega$; $T_{\text{j}} = 25^{\circ}\text{C}$	5.0.8
ON-Slew Rate ³⁾ (10 to 30% of V_{out}); V_{S} to GND transition of V_{IN}	SR_{ON}	—	—	6 ⁴⁾	V / μs	$V_{\text{S}} = 13.5\text{V}$; $R_{\text{L}} = 270\Omega$	5.0.9
ON-Slew Rate ³⁾ (10 to 30% of V_{out}); V_{S} to GND transition of V_{IN}	SR_{ON}	—	1.3	4.0	V / μs	$V_{\text{S}} = 13.5\text{V}$; $R_{\text{L}} = 270\Omega$; $T_{\text{j}} = 25^{\circ}\text{C}$	5.0.10
OFF-Slew Rate ³⁾ (70 to 40% of V_{out}); GND to V_{S} transition of V_{IN}	SR_{OFF}	—	—	8 ⁴⁾	V / μs	$V_{\text{S}} = 13.5\text{V}$; $R_{\text{L}} = 270\Omega$	5.0.11
OFF-Slew Rate ³⁾ (70 to 40% of V_{out}); GND to V_{S} transition of V_{IN}	SR_{OFF}	—	1.7	4.0	V / μs	$V_{\text{S}} = 13.5\text{V}$; $R_{\text{L}} = 270\Omega$; $T_{\text{j}} = 25^{\circ}\text{C}$	5.0.12

Standby current consumption

Electrical Characteristics

Table 4 $V_S = 9V$ to $60V$; $T_j = -40^\circ C$ to $125^\circ C$; all voltages with respect to ground. Currents flowing into the device unless otherwise specified in chapter "Block Diagram and Terms". Typical values at $V_S = 13.5V$, $T_j = 25^\circ C$

Parameter	Symbol	Values			Unit	Note / Test Condition	Number
		Min.	Typ.	Max.			
Standby current	I_{SOFF}	–	2	10	μA	IN open	5.0.13
Protection functions ⁵⁾							
Initial peak short circuit current limit IN connected to GND	I_{LSCP}	–	–	1.2	A	$T_j = -40^\circ C$; $V_S = 13.5V$ $t_m = 100\mu s$	5.0.14
Initial peak short circuit current limit IN connected to GND	I_{LSCP}	–	0.9	–	A	$T_j = 25^\circ C$; $V_S = 13.5V$ $t_m = 100\mu s$	5.0.15
Initial peak short circuit current limit IN connected to GND	I_{LSCP}	0.2	–	–	A	$T_j = 125^\circ C$; $V_S = 13.5V$ $t_m = 100\mu s$	5.0.16
Repetitive short circuit current limit IN connected to GND	I_{LSCR}	–	0.7	–	A	–	5.0.17
Output clamp at $V_{OUT} = V_S - V_{DSCL}$ (inductive load switch off)	V_{DSCL}	60	–	–	V	$I_S = 4mA$	5.0.18
Overvoltage protection	V_{SAZ}	62	68	–	V	$I_S = 1mA$	5.0.19
Thermal overload trip temperature ⁴⁾	T_{JTrip}	150	–	–	$^\circ C$	–	5.0.20
Thermal hysteresis ⁴⁾	T_{HYS}	–	10	–	$^\circ C$	–	5.0.21
Input interface							
Off state input current	I_{INOFF}	–	–	0.05	mA	$T_j = -25^\circ C$; $R_L = 270\Omega$; $V_{OUT} \leq 0.1V$	5.0.22
Off state input current	I_{INOFF}	–	–	0.04	mA	$T_j = 125^\circ C$; $R_L = 270\Omega$; $V_{OUT} \leq 0.1V$	5.0.23
On state input current; IN connected to GND ⁶⁾	I_{INON}	–	0.3	1.0	mA	–	5.0.24
Input resistance	R_{IN}	0.5	1.0	2.5	k Ω	–	5.0.25
Reverse Battery							
Continuous reverse drain current	I_{DREV}	–	–	0.2	A	–	5.0.26
Forward voltage of the drain-source reverse diode	V_{FDS}	–	600	–	mV	$I_{FDS} = 200mA$ $I_{IN} \leq 0.05mA$	5.0.27

- Nominal Load Current is limited by the current limitation; see protection function data
- Device on 50mm x 50mm x 1,5mm epoxy FR4 PCB with 6cm² (one layer copper 70um thick) copper area for supply voltage connection. PCB in vertical position without blown air
- Timing values only with high input slewrates ($t_{rIN} = t_{fIN} \leq 50ns$); otherwise slower
- Not tested in production
- Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.
- Driver circuit must be able to sink currents > 1mA

6 Application Information

6.1 Application Diagram

The following information is given as a hint for the implementation of the device only and shall not be regarded as a description or warranty for a certain functionality, condition or quality of the device.

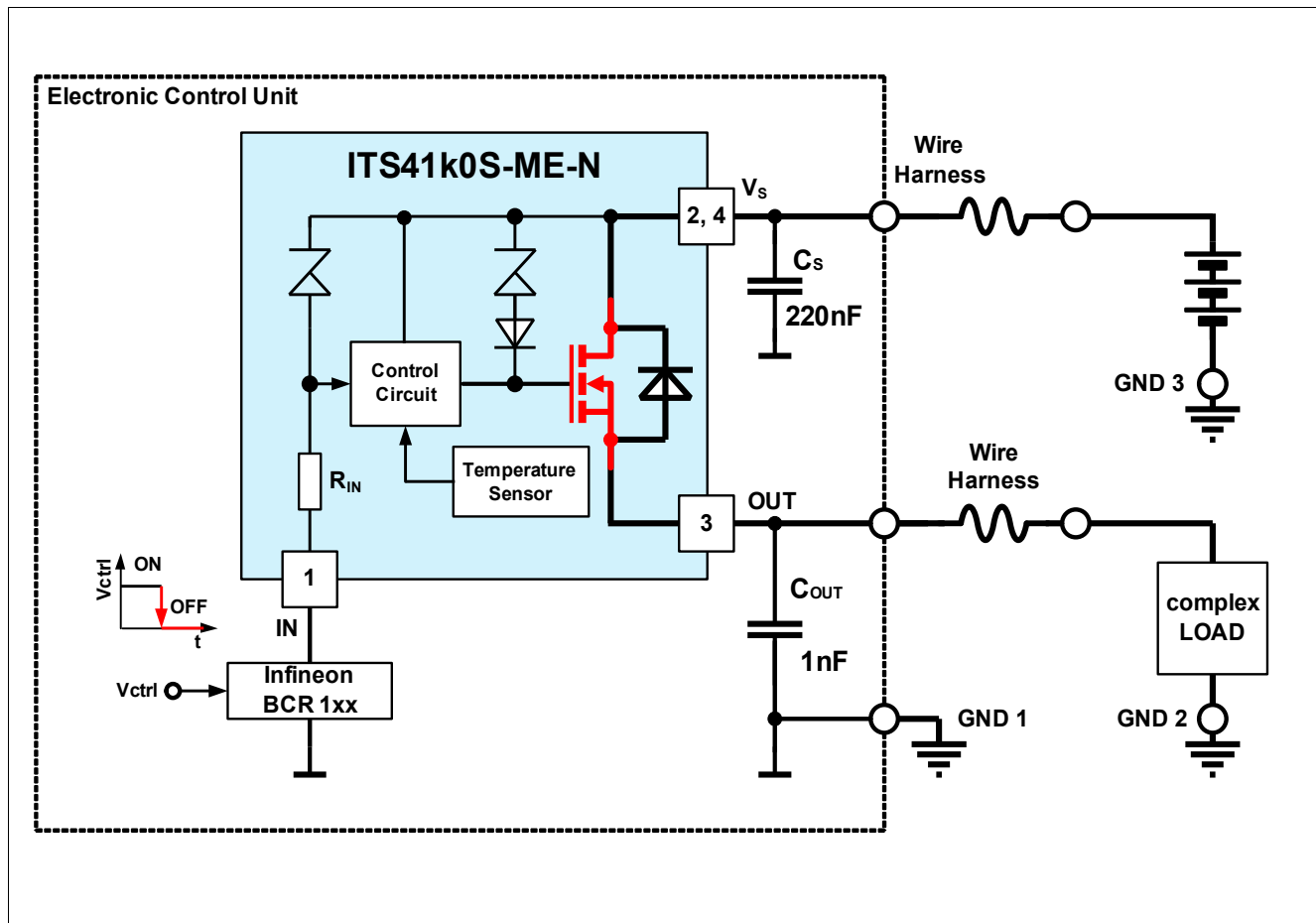


Figure 4 Application Diagram

The **ITS41k0S-ME-N** can be connected directly to a supply network. It is recommended to place a ceramic capacitor (e.g. $C_S = 220\text{nF}$) between supply and GND to avoid line disturbances. Wire harness inductors/resistors are sketched in the application circuit above.

The complex load (resistive, capacitive or inductive) must be connected to the output pin OUT.

A built-in current limit protects the device against destruction.

The **ITS41k0S-ME-N** can be switched on and off with a low power levelshifter switch e.g. Infineon BCR1xx.

The IN pin must be pulled down to GND potential to switch the **ITS41k0S-ME-N** on. If no current is pulled down, the IN-node will float up to V_S potential by an internal pull up. In this mode the **ITS41k0S-ME-N** is deactivated with very low current consumption.

The output voltage slope is controlled during on and off transistion to minimize emissions. Only a small C_{OUT}=1nF is recommended to attenuate RF noise.

In the following chapters the main features, some typical waveforms and the protection behaviour of the **ITS41k0S-ME-N** is shown. For further details please refer to application notes on the Infineon homepage.

6.2 Special features

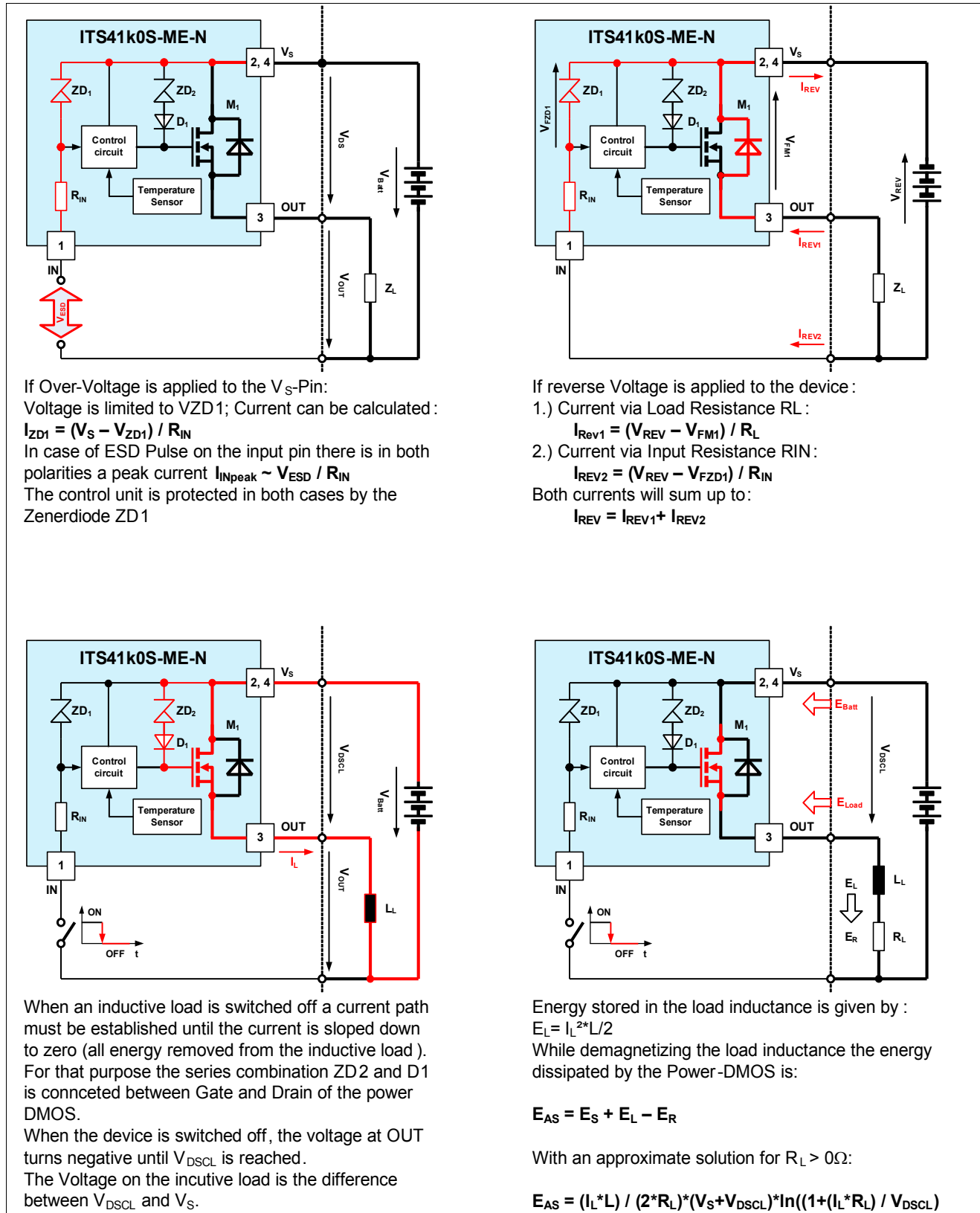


Figure 5 Special Feature descriptions

6.3 Typical Application Waveforms

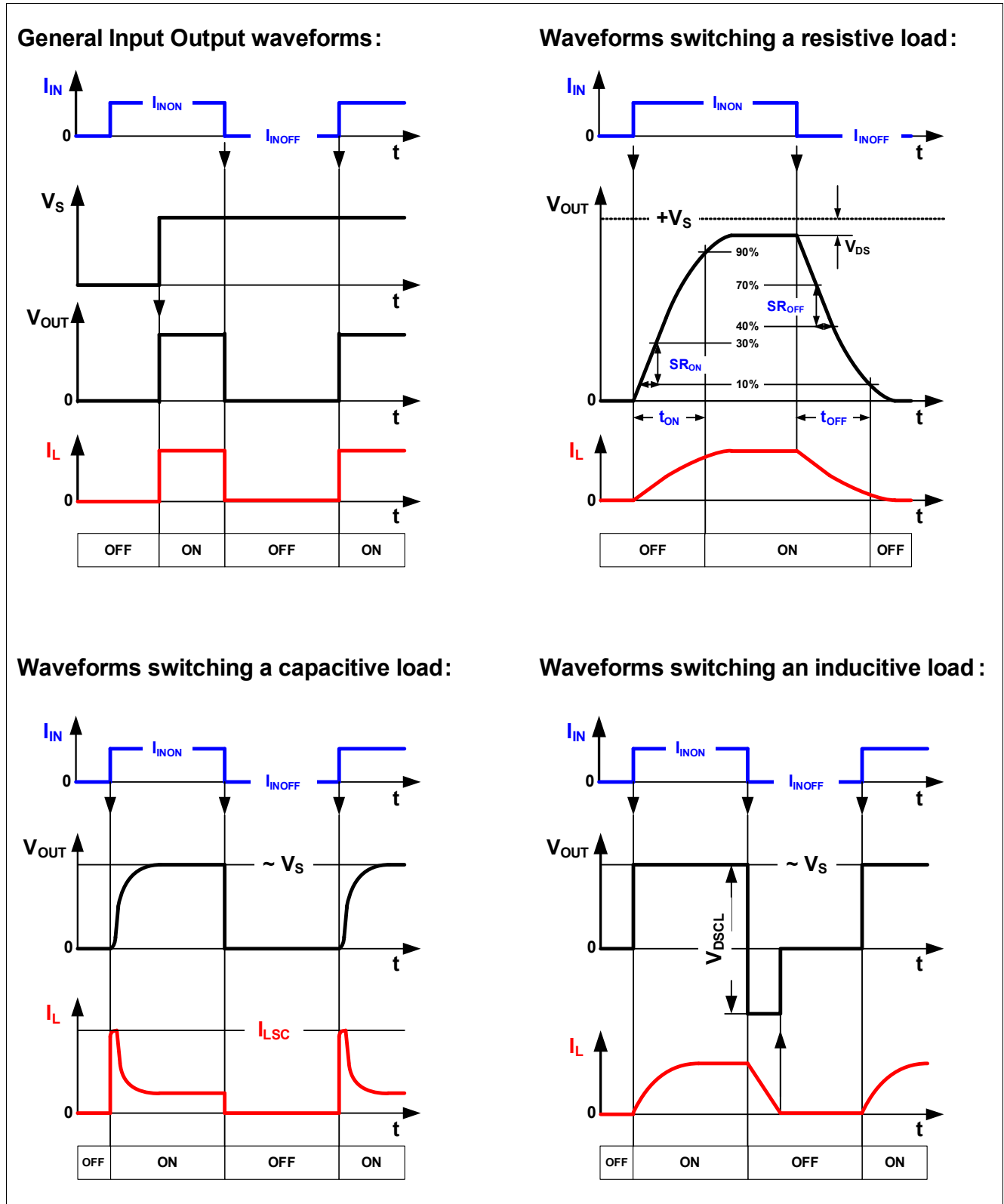


Figure 6 Typical application waveforms

6.4 Protection behavior

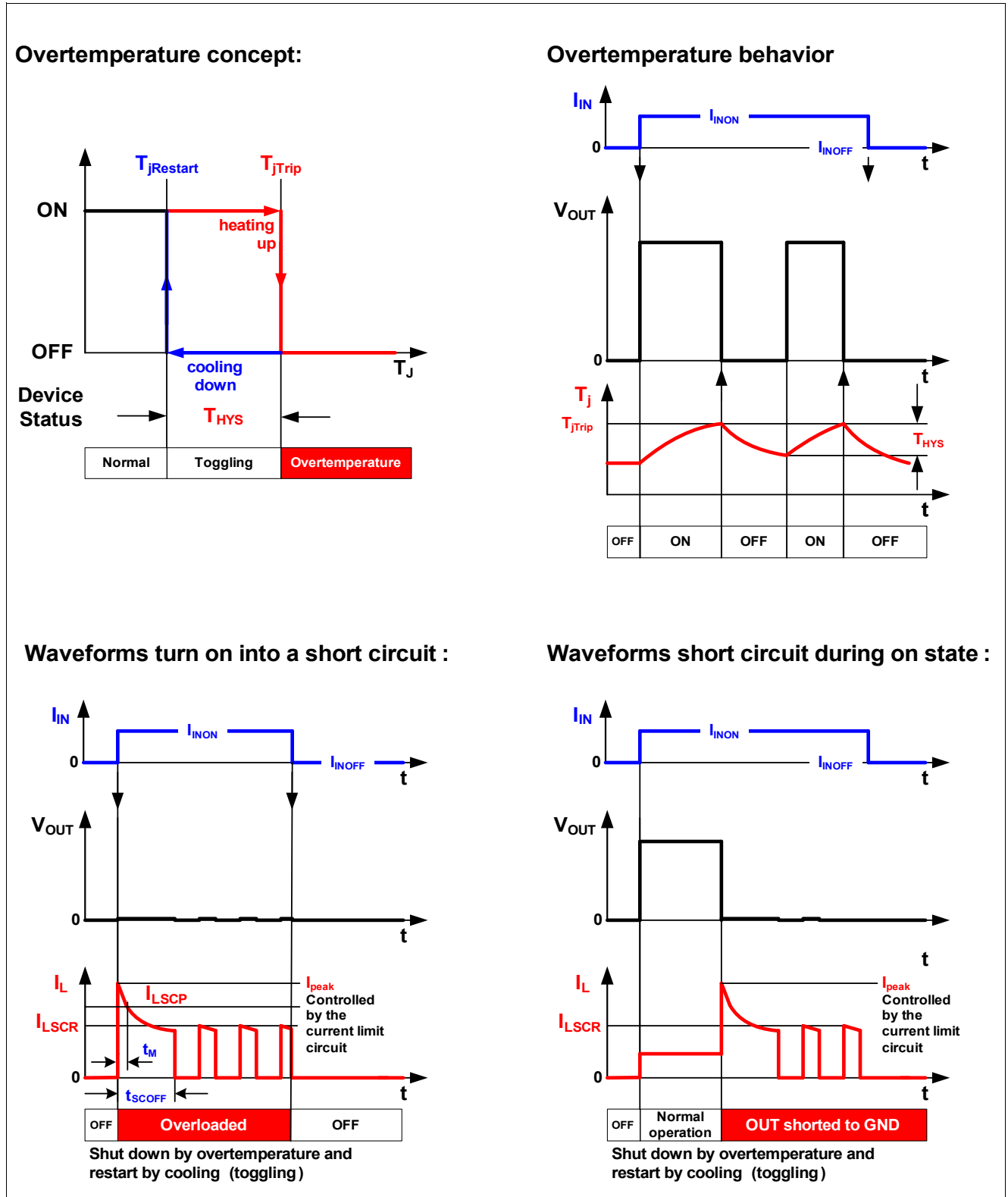
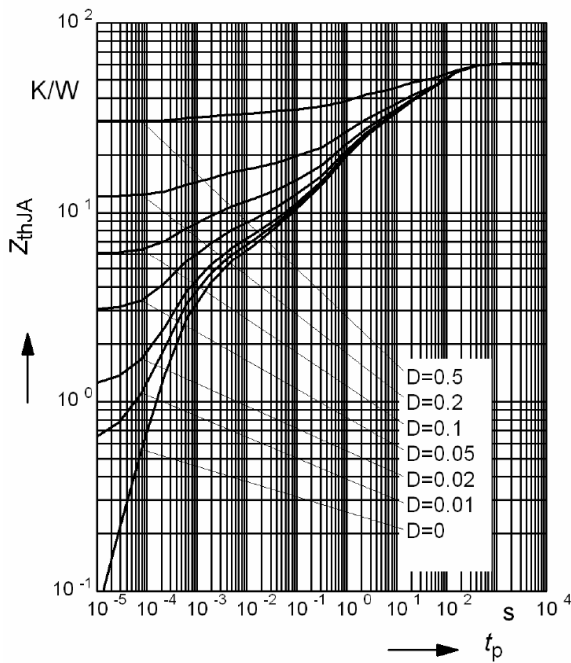


Figure 7 Protective behaviour waveforms of the ITS41k0S-ME-N

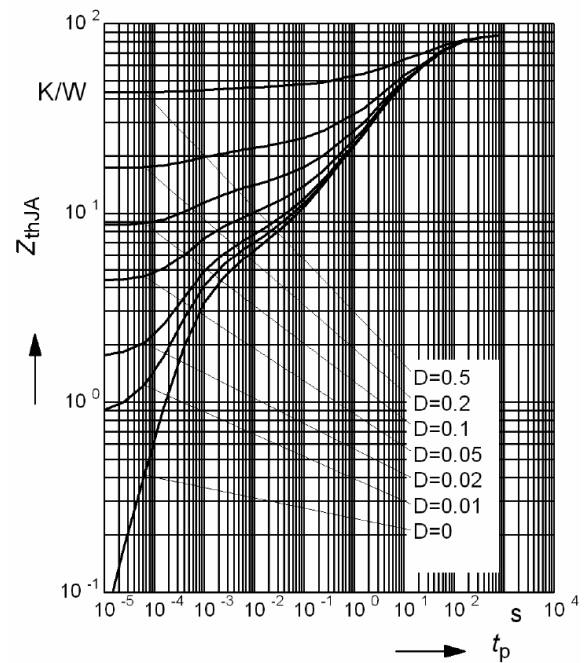
7 Typical Performance Graphs

Typical Performance Characteristics

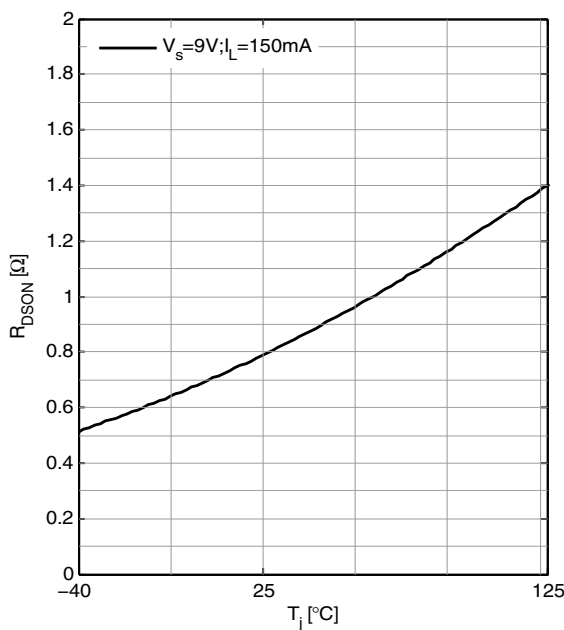
Transient Thermal Impedance Z_{thJA} versus Pulse Time t_p @ 6cm² heatsink area ($D = t_p/T$)



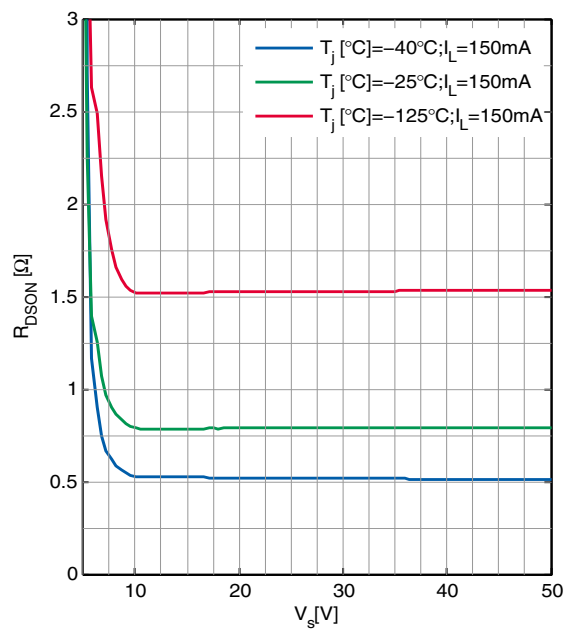
Transient Thermal Impedance Z_{thJA} versus Pulse Time t_p @ min. footprint ($D = t_p/T$)



On-Resistance $R_{DS(on)}$ versus Junction Temperature T_j @ $V_s = 9V$; $I_L = 150mA$



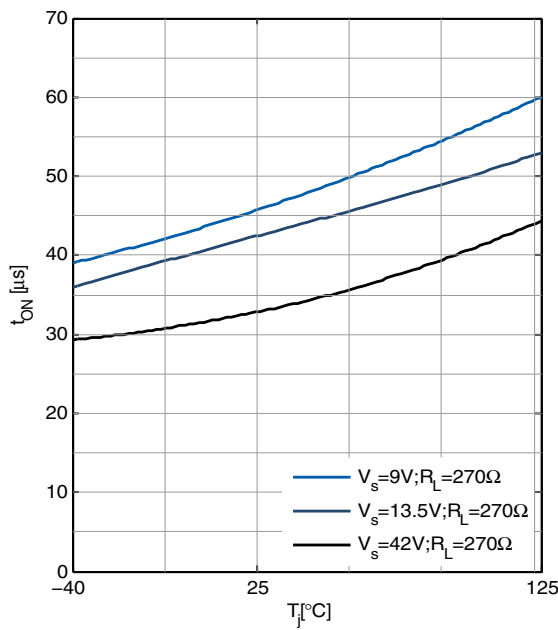
On-Resistance $R_{DS(on)}$ versus Supply Voltage $V_s = V_{bb}$ @ $I_L = 150mA$ $T_j = \text{par.}$



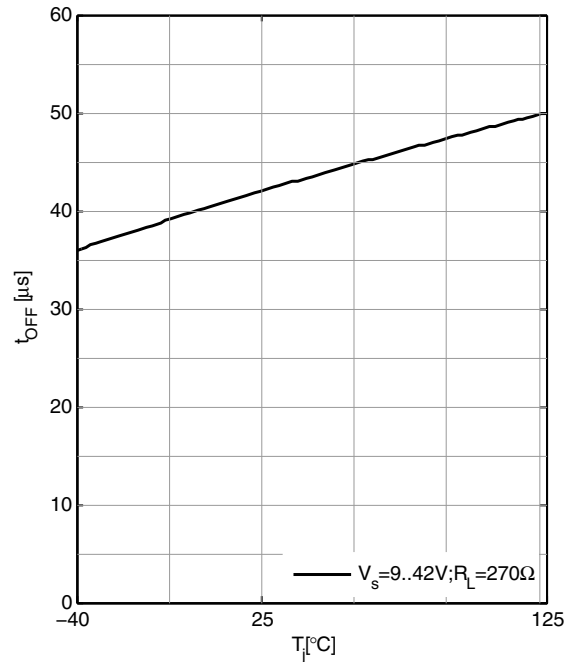
Typical Performance Graphs

Typical Performance Characteristics

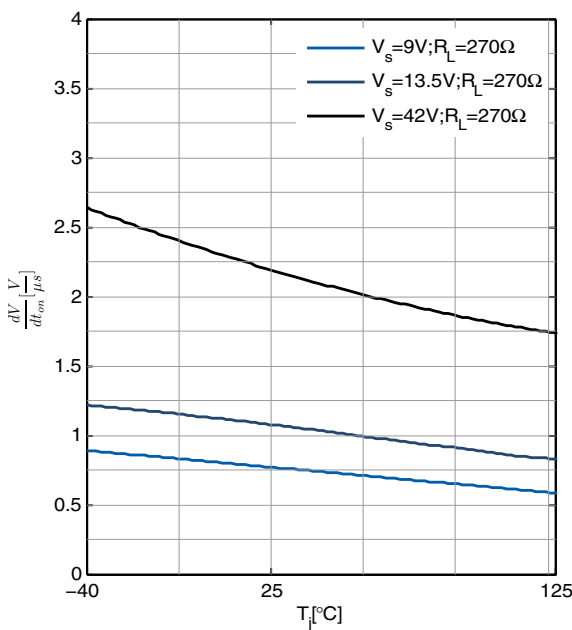
Switch ON Time t_{ON} versus
Junction Temperature T_J @ $R_L = 270 \Omega$; $V_S = \text{par.}$



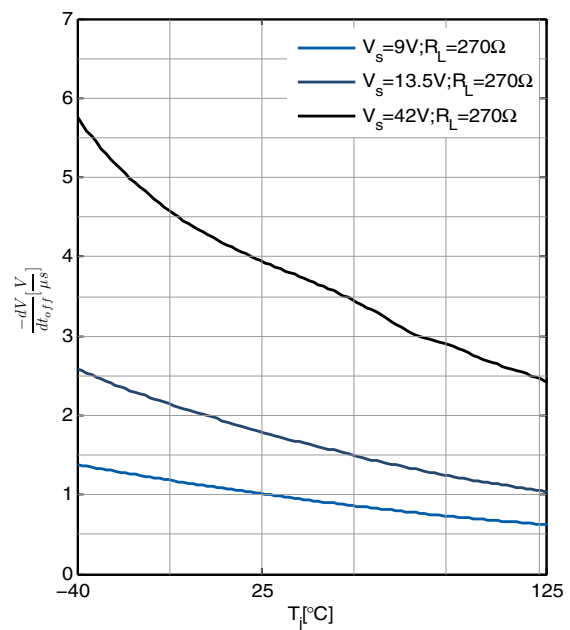
Switch OFF Time t_{OFF} versus
Junction Temperature T_J @ $R_L = 270 \Omega$; $V_S = \text{par.}$



ON Slewrate SR_{ON} versus
Junction Temperature T_J @ $R_L = 270 \Omega$; $V_S = \text{par.}$



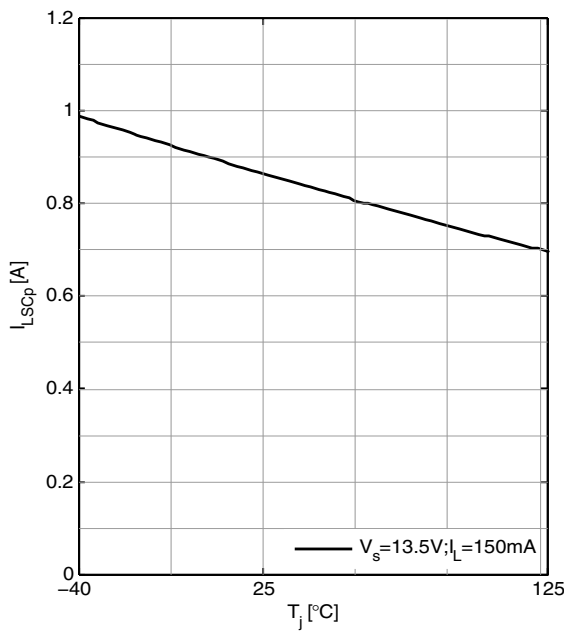
OFF Slewrate SR_{OFF} versus
Junction Temperature T_J @ $R_L = 270 \Omega$; $V_S = \text{par.}$



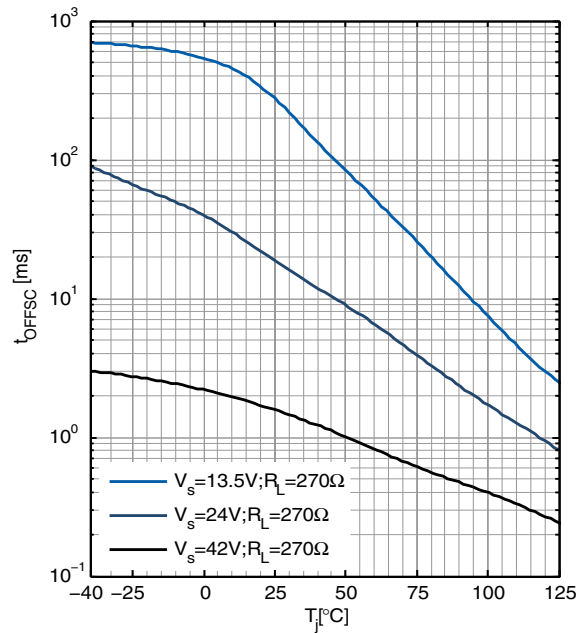
Typical Performance Graphs

Typical Performance Characteristics

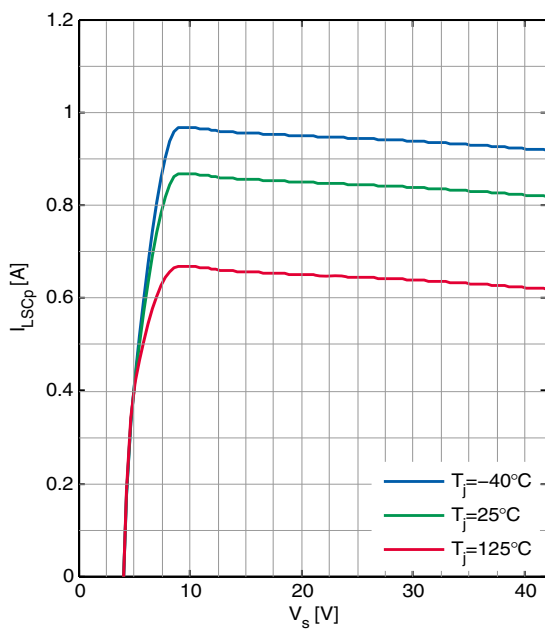
Initial Peak Short Circuit Current Limit I_{LSCP} versus Junction Temperature T_J @ $V_S=13.5V$; $t_m=100\mu s$



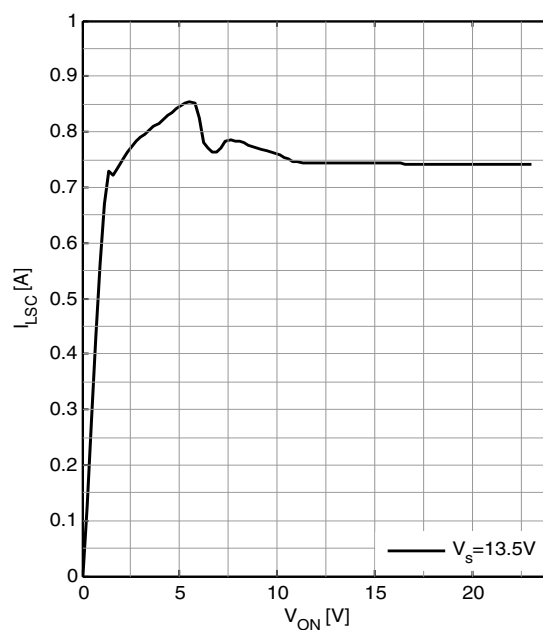
Initial Short Circuit Shutdown Time $t_{OFF SC}$ versus Junction Start-Temperature T_{JSTART} ; V_S =parameter



Initial Peak Short Circuit Current Limit I_{LSCP} versus Supply Voltage $V_S = V_{bb}$ @ T_J =par.= $100\mu s$.

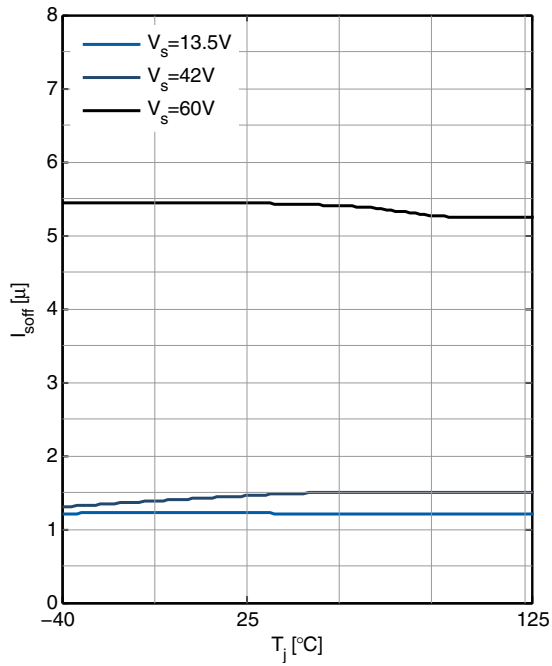


Current Limitation Characteristic I_{LSC} versus Drain Source Voltage Drop V_{DS} @ $V_S=13.5V$



Typical Performance Characteristics

Stand By Current Consumption I_{SOFF} versus
Junction Temperature T_J @ pin IN open



8 Package Outlines and Footprint

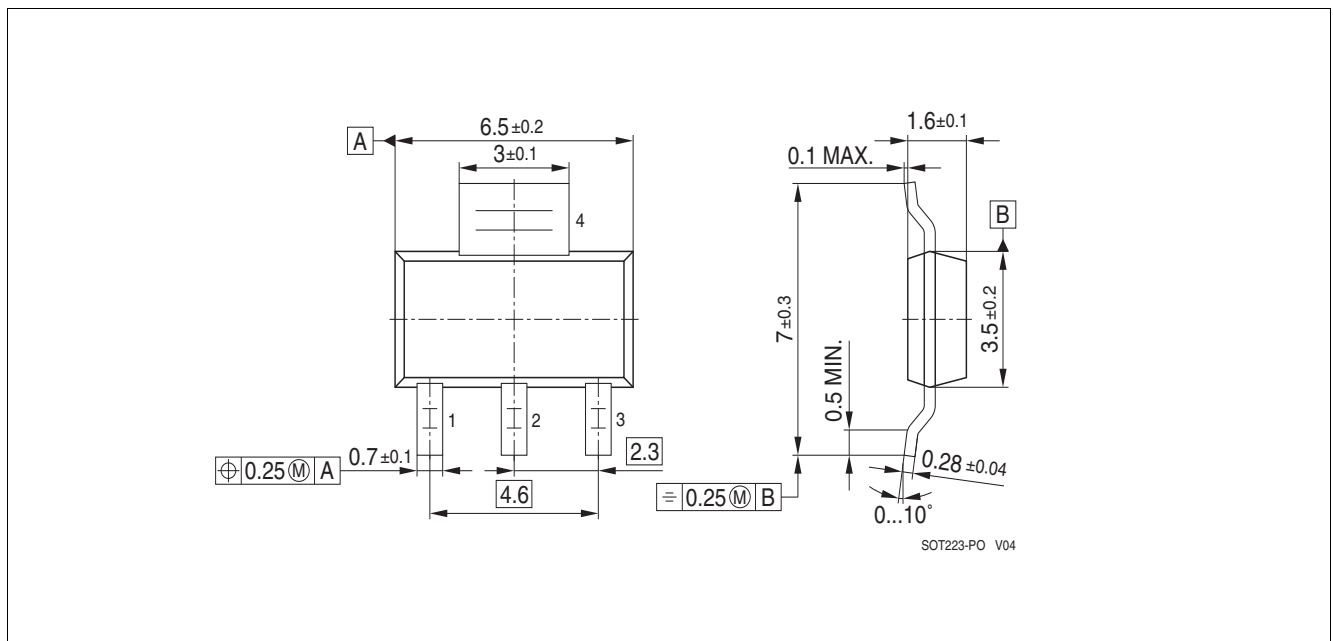


Figure 8 PG-SOT223-4 (Plastic Dual Small Outline Package, RoHS-Compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020)

9 Revision History

Revision	Date	Changes
1.0	2012-09-01	Datasheet release

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Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.